

DOUBLE DOPED-LAYER, PHOSPHORESCENT ORGANIC LIGHT EMITTING DEVICES

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FIELD OF THE INVENTION

The present invention is directed to double doped-layer, phosphorescent organic light emitting devices that are, for example, capable of emitting blue light. The present invention is directed to, for example, an organic light emitting device (OLED) over a substrate, where the OLED has an anode, a first hole transporting layer (HTL), a second hole transporting layer that is doped with a phosphorescent material, a first electron transporting layer (ETL) that is doped with a phosphorescent material, a second electron transporting layer, and a cathode.

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BACKGROUND OF THE INVENTION

Organic light emitting devices (OLEDs), which make use of thin film materials that emit light when excited by electric current, are expected to become an increasingly popular form of flat panel display technology. This is because OLEDs have a wide variety of potential applications, including cell phones, personal digital assistants (PDAs), computer displays, informational displays in vehicles, television monitors, as well as light sources for general illumination. Due to their bright colors, wide viewing angle, compatibility with full motion video, broad temperature ranges, thin and conformable form factor, low power requirements and the potential for low cost manufacturing processes, OLEDs are seen as a future replacement technology for cathode ray tubes (CRTs) and liquid crystal displays

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(LCDs), which currently dominate the growing \$40 billion annual electronic display market.

Due to their high luminous efficiencies, electrophosphorescent OLEDs are seen as having the potential to replace incandescent, and perhaps even fluorescent, lamps for certain types of applications.

5 Light emission from OLEDs is typically via fluorescence or phosphorescence.

As used herein, the term “phosphorescence” refers to emission from a triplet excited state of an organic molecule and the term “fluorescence” refers to emission from a singlet excited state of an organic molecule.

10 Successful utilization of phosphorescence holds enormous promise for organic electroluminescent devices. For example, an advantage of phosphorescence is that all excitons (formed by the recombination of holes and electrons in an emissive layer), which are formed either as a singlet or triplet excited state, may participate in luminescence. This is because the lowest singlet excited state of an organic molecule is typically at a slightly higher energy than the lowest triplet excited state. This means that, for typical phosphorescent organometallic compounds, the lowest singlet excited state may rapidly decay to the lowest triplet excited state from which the phosphorescence is produced. In contrast, only a small percentage (about 25%) of excitons in fluorescent devices are capable of producing the fluorescent luminescence that is obtained from a singlet excited state. The remaining excitons in a fluorescent device, which are produced in the lowest triplet excited state of an organic molecule, are typically not capable of being converted into the energetically unfavorable higher singlet excited states from which the fluorescence is produced. This energy, thus, becomes lost to radiationless decay processes that only tend to heat-up the device.

20 As a consequence, since the discovery that phosphorescent materials can be used as the emissive material in highly efficient OLEDs, there is now much interest in finding

still more efficient electrophosphorescent materials and OLED structures containing such materials.

High efficiency organic light emitting devices (OLEDs) using the phosphorescent dopant, *fac* tris(2-phenylpyridine)iridium (Ir(ppy)_3), have been demonstrated using several different conducting host materials. M. A. Baldo et al., *Nature*, vol. 395, 151 (1998); D. F. O'Brien et al., *Appl. Phys. Lett.*, vol. 74, 442 (1999); M. A. Baldo et al., *Appl. Phys. Lett.*, vol. 75, 4 (1999); T. Tsutsui et al., *Japanese. J. Appl. Phys., Part 2*, vol. 38, L1502 (1999); C. Adachi et al., *Appl. Phys. Lett.*, vol. 77, 904 (2000); M. J. Yang et al., *Japanese J. Appl. Phys., Part 2*, vol. 39, L828 (2000); and C. L. Lee et al., *Appl. Phys. Lett.*, vol. 77, 2280 (2000). Since the triplet level of the metal-ligand charge transfer state of the green-emitting Ir(ppy)_3 is between 2.5 eV and 3.0 eV, deep blue fluorophores with a peak wavelength at about 400 nm, such as 4,4'-*N,N'*-dicarbazole-biphenyl (CBP), are likely candidates as triplet energy transfer and exciton confining media. Using 6% to 10% Ir(ppy)_3 in CBP leads to efficient Ir(ppy)_3 phosphorescence. In addition to the energetic resonance between the dopant and the host, the control of charge carrier injection and transport in the host layers is believed to be necessary for achieving efficient formation of radiative excitons. High electrophosphorescence efficiency has been achieved using Ir(ppy)_3 doped into CBP along with a 2,9-dimethyl-4,7-diphenyl-phenanthroline (BCP) electron transport and exciton blocking layer. M. A. Baldo et al., *Appl. Phys. Lett.*, vol. 75, 4 (1999). In that device, the doped CBP layer was found to readily transport holes.

Current materials used in phosphorescent OLEDs may be used to form devices with internal quantum efficiencies of near 100%. However, the materials used to form the hole transporting, recombination and blocking layers in these conventional devices tend to have triplet energies corresponding to emission in the green part of the spectrum. If a dopant

capable of producing blue phosphorescence is inserted in such a device utilizing the existing materials and structures, the emission will only come, if at all, inefficiently from the matrix material, and not from the phosphorescent dopant material. Accordingly, there is great interest in finding efficient OLED structures that can emit in the blue region of the visible electromagnetic spectrum.

SUMMARY OF THE INVENTION

The present invention is directed to phosphorescent OLEDs having a double doped-layer structure. The OLEDs of the present invention typically have an anode, a first hole transporting layer (HTL) over the anode, a second HTL that is doped with a phosphorescent material over the first HTL, a first electron transporting layer (ETL) that is doped with a phosphorescent material over the second HTL, a second ETL over the first ETL, and a cathode over the second ETL. In each embodiment of the present invention, the OLED includes an HTL having a phosphorescent material doped therein, and an ETL having the same phosphorescent material doped therein.

The present invention is directed to phosphorescent OLEDs having a double doped-layer structure that preferably emit light in the blue range of the visible spectrum. The phosphorescent OLEDs of the present invention preferably include blue phosphorescent OLEDs with high efficiency levels.

BRIEF DESCRIPTION OF THE DRAWINGS

Figure 1 is a graph showing the electroluminescent (EL) intensity as a function of wavelength for: (1) an OLED having a ITO/R854 (450Å)/TAZ:6%-Ir(4,6-F₂ppy)(pico) (250Å)/Alq₃ (450Å)/MgAg layer structure (Host #1); and (2) an OLED having a ITO/R854

(400Å)/R854:6%-Ir(4,6-F₂ppy)(pico) (200Å)/TAZ:6%-Ir(4,6-F₂ppy)(pico) (200Å)/Alq₃
(400Å)/MgAg layer structure (Host #2).

Figure 2 is a graph showing: (1) the external quantum efficiency (η_{ext}) as a function of current density, and (2) the power efficiency (η_p) as a function of current density, each for an OLED having a ITO/R854 (400Å)/R854:6%-Ir(4,6-F₂ppy)(pico) (200Å)/TAZ:6%-Ir(4,6-F₂ppy)(pico) (200Å)/Alq₃ (400Å)/MgAg layer structure.

DETAILED DESCRIPTION

The present invention will be described with reference to the illustrative embodiments in the following description. These embodiments are intended only as illustrative examples and the invention is not to be limited thereto.

The present invention relates to a phosphorescent organic light emitting device (OLED) having a double doped-layer structure. That is, in each embodiment of the present invention, the OLED includes a hole transporting layer (HTL) having a phosphorescent material doped therein, and an electron transporting layer (ETL) having the same phosphorescent material doped therein. For example, an OLED of the present invention can be comprised of an anode, a first HTL, a second HTL that is doped with a phosphorescent material, a first ETL that is doped with a phosphorescent material, a second ETL, and a cathode. According to the present invention, the phosphorescent dopant of the hole transporting layer is the same material as the phosphorescent dopant of the electron transporting layer. The material constituting the first HTL need not be the same material as that constituting the second HTL, and the material constituting the first ETL need not be the same material as that constituting the second ETL. As would be understood by one skilled in the art, a hole transporting material is one in which charge carrier transport is predominantly

by the transport of holes and an electron transporting material is one for which charge carrier transport is predominantly by the transport of electrons.

In one embodiment of the present invention, the OLED structure includes a substrate, an anode over the substrate, a first HTL over the anode, a second HTL that is doped with a phosphorescent material over the first HTL, a first ETL that is doped with a phosphorescent material over the second HTL, a second ETL over the first ETL, and a cathode over the second ETL.

In another embodiment of the present invention, the OLED structure includes an inverted OLED over a substrate. In this embodiment, a cathode is positioned over the substrate, a second ETL over the cathode, a first ETL over the second ETL, a second HTL over the first ETL, a first HTL over the second HTL, and a cathode over the first HTL. The second HTL and the first ETL are doped with a phosphorescent material. Alternatively, in still another embodiment, an inverted OLED may comprise an HTL doped with a phosphorescent material and an ETL doped with a phosphorescent material.

For example, the first hole transporting layer may function substantially as a hole injecting layer (HIL). The hole injecting materials of the present invention may be characterized as materials that planarize or wet the anode surface so as to provide efficient hole injection from the anode into the hole injecting material. The hole injecting materials of the present invention are further characterized as having HOMO (Highest Occupied Molecular Orbital) energy levels that favorably match up, as defined by their herein-described relative IP energies, with the adjacent anode layer on one side of the HIL layer and the phosphorescent-doped hole transporting layer on the opposite side of the HIL.

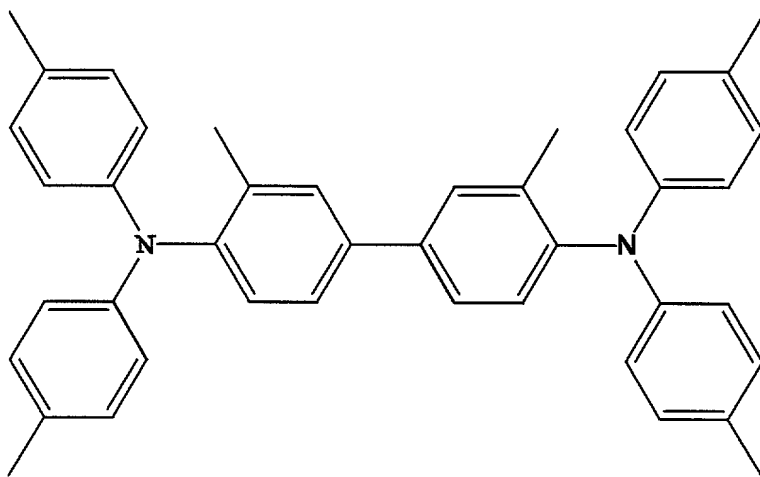
Preferred properties for the HIL material are such that holes can be efficiently injected from the anode into the HIL material. In particular, the HIL material preferably has an

IP not more than about 0.7 eV greater than the IP of the anode material. More preferably, the HIL material has an IP not more than about 0.5 eV greater than the anode material.

The HIL materials are further distinguished from conventional hole transporting materials that are typically used in the hole transporting layer of an OLED in that such HIL materials have a hole mobility that is substantially less than the hole mobility of conventional hole transporting materials. For example, m-MTDATA has been identified as effective in promoting injection of holes from ITO into HTLs consisting of, for example 4,4'-bis[N-(naphthyl)-N-phenyl-amino]biphenyl (α -NPD) or N,N'-bis(3-methylphenyl)-N,N'-diphenyl-[1,1'-biphenyl]4,4'-diamine (TPD), possibly due to reduction of the HTL HOMO level/ITO offset energy, or to wetting of the ITO surface. The HIL material m-MTDATA is believed to have a hole mobility of about $3 \times 10^{-5} \text{ cm}^2/\text{Vsec}$ as compared with the conventional hole transporting materials such as α -NPD or TPD, which have a hole mobility of about $5 \times 10^{-4} \text{ cm}^2/\text{Vsec}$ and $9 \times 10^{-4} \text{ cm}^2/\text{Vsec}$, respectively. Thus, the m-MTDATA material has a hole mobility more than an order of magnitude less than the commonly used HTL materials α -NPD and TPD.

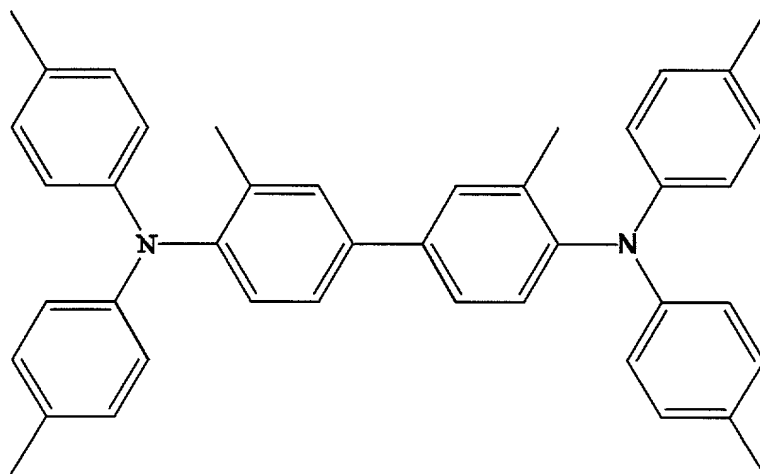
In those embodiments of the present invention containing two HTLs, the first HTL may include any suitable material that acts as a good transporter of charge (*i.e.*, holes). Suitable hole transporting materials are known in the art, and examples of materials that may be suitable for the first hole transporting layer can be found in U.S. Patent No. 5,707,745, which is incorporated herein in its entirety by reference. Other materials suitable for use as the first hole transporting layer may include, for example, 4,4'-bis[N-(1-naphthyl)-N-phenyl-amino]biphenyl (α -NPD); N,N'-diphenyl-N,N'-bis(3-methylphenyl)-1,1'-biphenyl-4,4'-diamine (TPD); 4,4'-bis[N,N'-(3-tolyl)amino]-3,3'-dimethylbiphenyl (M14); 4,4',4''-tris(3-methylphenylphenylamino)triphenylamine (MTDATA); and 4,4'-bis[N,N'-(3-

tolyl)amino]-3,3'-dimethylbiphenyl (HMTDP). In a preferred embodiment, the first hole transporting layer is 3,3'-Dimethyl- N,N,N',N' -tetra-*p*-tolyl-biphenyl-4,4'-diamine (R854) having the following chemical formula:

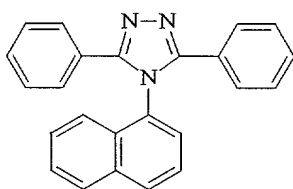


The second HTL, which is doped with a phosphorescent material and is an emissive layer (EML), may include any suitable material that acts as a good transporter of charge (*i.e.*, holes) and also efficiently transfers energy to a highly luminescent guest. Suitable hole transporting materials are known in the art, and examples of materials that may be suitable for the second hole transporting layer can be found in U.S. Patent No. 5,707,745, which, as indicated above, is incorporated herein in its entirety by reference. Other materials

suitable for use as the second hole transporting layer may include, for example, 4,4'-bis[*N*-(1-naphthyl)-*N*-phenyl-amino]biphenyl (α -NPD); N,N'-diphenyl-N,N'-bis(3-methylphenyl)1-1'-biphenyl-4,4'-diamine (TPD); 4,4'-bis[N,N'-(3-tolyl)amino]-3,3'-dimethylbiphenyl (M14); 4,4',4''-tris(3-methylphenylphenylamino)triphenylamine (MTDATA); and 4,4'-bis[N,N'-(3-tolyl)amino]-3,3'-dimethylbiphenyl (HMTDP). In one preferred embodiment, the second hole transporting layer is 3,3'-Dimethyl-*N,N,N',N'*-tetra-*p*-tolyl-biphenyl-4,4'-diamine (R854) having the following chemical formula:



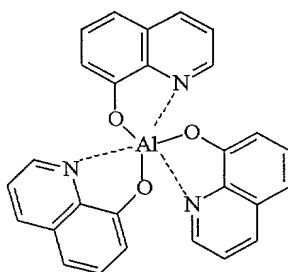
The first ETL, which is doped with a phosphorescent material and is an emissive layer (EML), may include any suitable host material that acts as a good transporter of charge (*i.e.*, electrons) and also efficiently transfers energy to a highly luminescent guest. Suitable electron transporting materials are known in the art, and examples of materials that may be suitable for the first electron transporting layer can be found in the co-pending application U.S. Serial No. 09/629,335 filed on August 1, 2000, which is incorporated herein in its entirety by reference. Examples of materials suitable for use as the first electron transporting layer may include, for example, an oxadiazole such as 1,3-bis (N,N-t-butyl-phenyl)-1,3,4-oxadiazole (OXD-7), an oxadiazole derivative, a phenanthroline such as 2,9-dimethyl-4,7-diphenyl-1,10-phenanthroline (bathocuproine or BCP), a BCP derivative, or a substituted or un-substituted benzoxazole or benzthiazole compound. In a preferred embodiment, the first electron transporting layer is a host material of 3-phenyl-4-(1'-naphthyl)-5-phenyl-1,2,4-triazole (TAZ) having the following chemical formula:



In those embodiments of the present invention containing two ETLs, the second ETL may include any suitable material that acts as a good transporter of charge (*i.e.*, electrons), and that also functions as an effective electron injecting layer (EIL). Suitable

electron transporting materials are known in the art, and examples of materials that may be suitable for the second ETL can be found in U.S. Patent No. 5,707,745, which, as indicated above, is herein incorporated in its entirety by reference. In a preferred embodiment, the second ETL is comprised of the electron transporting material tris-(8-

5 hydroxyquinoline)aluminum (Alq_3), which is used to transport electrons into the first electron transporting layer, and has the following chemical formula:

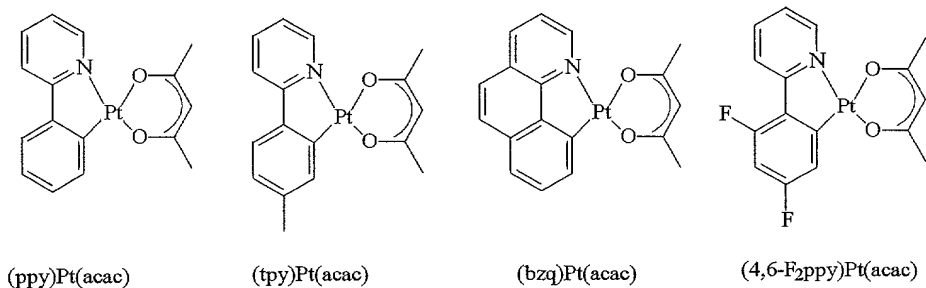


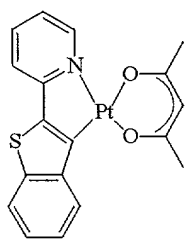
An effective electron injecting layer may be comprised of a phthalocyanine compound, for example, copper phthalocyanine (CuPc).

10 In addition to functioning as an electron injecting layer, the second ETL may also function as a hole blocking layer and/or as an exciton blocking layer. The hole blocking and/or exciton blocking layer in OLED devices substantially blocks the diffusion of holes and/or excitons, respectively, thus substantially keeping the holes and/or excitons,

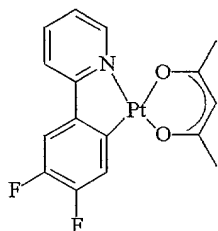
respectively, within the emissive region of the device so as to enhance device efficiency.

Any phosphorescent emitters may be used as phosphorescent dopants in the present invention. Preferred phosphorescent dopants are those organometallic complexes disclosed in the co-pending application U.S. Serial No. 09/637,766 filed on August 11, 2000, which is herein incorporated in its entirety by reference. Examples of such preferred phosphorescent dopants include Platinum(II) (2-phenylpyridinato-N,C^{2'}) (acetyl acetonate) [Pt(ppy)(acac)], Platinum(II) (2-(p-tolyl)pyridinato-N,C^{2'}) (acetyl acetonate) [Pt(tpy)(acac)], Platinum(II) (7,8-benzoquinolinato-N,C^{3'}) (acetyl acetonate) [Pt(bzq)(acac)], Platinum(II) (2-(2'-(4',5'-benzothienyl)pyridinato-N,C^{3'}) (acetyl acetonate) [Pt(btp)(acac)], Platinum(II) (2-(4',6'-difluorophenyl)pyridinato-N,C^{2'}) (acetyl acetonate) [Pt(4,6-F₂ppy)(acac)], Platinum(II) (2-(4',5'-difluorophenyl)pyridinato-N,C^{2'}) (acetyl acetonate) [Pt(4,5-F₂ppy)(acac)], and Platinum(II) (2-(4',5'-difluorophenyl)pyridinato-N, C^{2'}) (2-picolinato) [Pt(4,5-F₂ppy)(pico)], whose corresponding chemical structures can be seen below as follows:

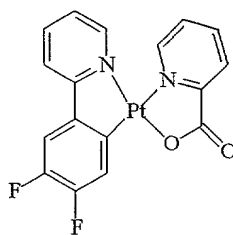




(btp)Pt(acac)



(4,5-F₂ppy)Pt(acac)



(4,5-F₂ppy)Pt(pico)

Another preferred phosphorescent dopant is Iridium (2-(4',6'-difluorophenyl)pyridinato-N,C^{2'}) (2-picolinato) [Ir(4,6-F₂ppy)(pico)], which is used as the phosphorescent dopant in the example of the present invention which is discussed later in this Detailed Description.

In the OLED structures of the present invention, light may be emitted from the substrate side of the device, or alternatively, from the side of the device opposite the substrate, that is, as a top-emitting device. A top-emitting device is one which has an opaque and/or reflective substrate such that light is produced only out of the top of the device and not through the substrate. The substrate is typically referred to as being at the bottom of the device.

Substrates according to the present invention may be opaque or substantially transparent, rigid or flexible, and/or plastic, metal or glass. Although not limited to the thickness ranges recited herein, the substrate may be as thin as 10 mm if present as a flexible plastic or metal foil substrate, or substantially thicker if present as a rigid, transparent or opaque substrate, or if the substrate is made of silicon.

Suitable electrode (*i.e.*, anode and cathode) materials include conductive materials such as a metal, a metal alloy or ITO which form electrical contacts. The deposition of electrical contacts may be accomplished by vapor deposition or other suitable metal

deposition techniques. These electrical contacts may be made, for example, from indium, magnesium, platinum, gold, silver or combinations such as Ti/Pt/Au, Cr/Au or Mg/Ag.

When depositing the top electrode layer (*i.e.*, the cathode or the anode, typically the cathode), that is, the electrode on the side of the OLED furthest from the substrate, damage to the organic layers should be avoided. For example, organic layers should not be heated above their glass transition temperature. Top electrodes are preferably deposited from a direction substantially perpendicular to the substrate.

In preferred embodiments, the cathode is preferably a low work function, electron-injecting material, such as a metal layer. Preferably, the cathode material has a work function that is less than about 4 electron volts. The cathode preferably is a metal layer of about 100 Å (angstroms) thick or less, and may be about 50 Å thick or less. The contacts are preferably made of magnesium silver or a magnesium and silver alloy. The metal cathode layer may be substantially thicker if the cathode layer is opaque.

For top-emitting devices, a transparent cathode such as disclosed in U.S. Patent No. 5,703,436, or co-pending patent applications U.S. Serial Nos. 08/964,863 and 09/054,707, may be used. A transparent cathode has light transmission characteristics such that the OLED has an optical transmission of at least about 50%. Preferably, the transparent cathode has light transmission characteristics that permit the OLED to have an optical transmission of at least about 70%, more preferably, at least about 85%.

The anode is preferably a high work function hole-injecting metal anode layer, for example, an indium tin oxide (ITO) layer. ITO is a transparent conductor which functions as an anode. ITO is a degenerate semiconductor formed by doping a wide band semiconductor. The carrier concentration of the ITO is in excess of $10^{19}/\text{cm}^3$. The ITO anode layer may be about 500 Å to greater than about 4000 Å thick. For top-emitting devices that

use an opaque or reflective anode, a high-work-function metal such as Au may be used.

It is desirable for the OLEDs of the present invention to be fabricated using materials that provide electroluminescent emission in a relatively narrow band centered near selected spectral regions, which correspond to one of the three primary colors, red, green and blue so that they may be used as a colored layer in an OLED. It is also desirable that such compounds be capable of being readily deposited as a thin layer using vacuum deposition techniques so that they may be readily incorporated into an OLED that is prepared entirely from vacuum-deposited organic materials.

The OLEDs and OLED structures of the present invention optionally contain additional materials or layers depending on the desired effect, such as protective layers (to protect certain materials during the fabrication process), insulating layers, reflective layers to guide waves in certain directions, and protective caps, which cover the electrodes and organic layers in order to protect these layers from the environment. A description of insulating layers and protective caps is contained for example, in U.S. Patent No. 6,013,538, which is hereby incorporated by reference in its entirety.

There may be substantial variation of the type, number, thickness and order of the layers that are present, dependent on whether an inverted sequence of OLED layers is present, whether the OLED is intended to produce emission in a preferred spectral region, or whether still other design variations are used.

This invention will now be described in detail with respect to showing how a certain specific representative embodiment thereof can be made, the materials, apparatus and process steps being understood as examples that are intended to be illustrative only. In particular, the invention is not intended to be limited to the methods, materials, conditions, process parameters, apparatus and the like specifically recited herein.

EXAMPLE 1

A first HTL is first deposited onto an ITO (indium tin oxide) coated glass substrate. The first HTL consists of about 400 Å of R854. A second HTL consists of about 200 Å of R854, and is deposited onto the first HTL. The second HTL is about 6% doped with Ir(4,6-F₂ppy)(pico). A first ETL consists of about 200 Å of TAZ, and is deposited onto the second HTL. The first ETL is about 6% doped with Ir(4,6-F₂ppy)(pico). A second ETL of Alq₃ having a thickness of about 400 Å is deposited onto the first ETL. The device is finished by depositing a Mg/Ag electrode onto the second ETL. This Mg/Ag electrode has a thickness of about 100 nm. All of the depositions are carried out at a vacuum less than 5 X 10⁻⁵ Torr. The devices are tested in air, without packaging.

Figure 1 shows a depiction of the EL intensity as a function of wavelength for two different OLEDs. The first OLED (Host #1) has a ITO/R854 (450Å)/TAZ:6%-Ir(4,6-F₂ppy)(pico) (250Å)/Alq₃ (450Å)/MgAg layer structure, and the second OLED (Host #2) has a structure according to Example 1 above. That is, the first OLED and the second OLED are similar in structure except that the first OLED lacks the second hole transporting layer doped with a phosphorescent material which is present in the second OLED, representative of Example 1. As can be seen in Figure 1, although both OLEDs display a peak EL intensity at about 472 nm, the first OLED (lacking the second HTL doped with a phosphorescent material) has an additional peak intensity at about 400 nm. Elimination of this additional peak helps to enhance overall device efficiency. Furthermore, it is believed that use of adjacent phosphorescent-doped layers may also help enhance device efficiency by eliminating exciplex formation.

Figure 2 shows the external quantum efficiency (η_{ext}) of a 6%-Ir(4,6-

F₂ppy)(pico)-doped R854 / 6%-Ir(4,6-F₂ppy)(pico)-doped TAZ device. A maximum η_{ext} of about 2% was obtained, at a current density of about 0.1 to 1.0 mA/cm², with CIE values of X=0.14 and Y=0.32.

It is believed this is the first reported evidence of electrophosphorescence in the blue region of the spectrum. Furthermore, it is believed that an external quantum efficiency of 2% shows that still higher quantum efficiencies may ultimately be achieved using the materials and device structures as described herein to produce blue electrophosphorescence.

Figure 2 also shows the power efficiency (η_p) of a 6%-Ir(4,6-F₂ppy)(pico)-doped R854 / 6%-Ir(4,6-F₂ppy)(pico)-doped TAZ device. A maximum η_p of about 2.5 lm/W was obtained, at a current density of about 0.1 mA/cm².

The structures of the present invention may be used for example, in substantially any type of device that includes one or more OLEDs including billboards and signs, computer monitors, vehicles, telecommunications devices, telephones, printers televisions, large area wall screens, theater screens and stadium screens.

While the present invention is described with respect to particular examples and preferred embodiments, it is understood that the present invention is not limited to these examples and embodiments. In particular, the present invention may be applied to a wide variety of electronic devices. The present invention as claimed therefore includes variations from the particular examples and preferred embodiments described herein, as will be apparent to one of skill in the art.